

Silicon PNP Power Transistors

2N5676

DESCRIPTION

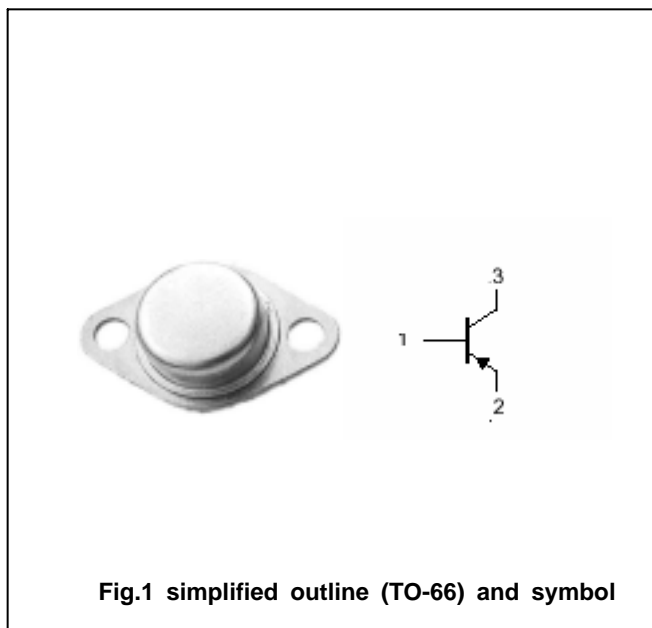
- With TO-66 package
- High transition frequency

APPLICATIONS

- For use as high-frequency drivers in audio amplifiers

PINNING

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector



Absolute maximum ratings(Ta=)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	-125	V
V _{CEO}	Collector-emitter voltage	Open base	-100	V
V _{EBO}	Emitter-base voltage	Open collector	-5	V
I _C	Collector current		-2	A
P _D	Total Power Dissipation	T _C =25	2	W
T _j	Junction temperature		150	
T _{stg}	Storage temperature		-65~200	

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
R _{th j-c}	Thermal resistance junction to case	2.5	/W

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-emitter sustaining voltage	I _C =-0.1A ; I _B =0	-100			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =-1A; I _B =-0.1A			-0.5	V
V _{BEsat}	Base-emitter saturation voltage	I _C =-1A ; I _B =-0.1A			-1.2	V
V _{BE}	Base-emitter on voltage	I _C =-1A ; V _{CE} =-5V			-1.2	V
I _{CEO}	Collector cut-off current	V _{CE} =-50V; I _B =0			-0.5	mA
I _{CBO}	Collector cut-off current	V _{CB} =-125V; I _E =0			-0.1	mA
I _{EBO}	Emitter cut-off current	V _{EB} =-5V; I _C =0			-0.1	mA
h _{FE-1}	DC current gain	I _C =-0.1A ; V _{CE} =-5V	50			
h _{FE-2}	DC current gain	I _C =-0.5A ; V _{CE} =-5V	50		150	
f _T	Transition frequency	I _C =-100mA; V _{CE} =10V	50			MHz

PACKAGE OUTLINE

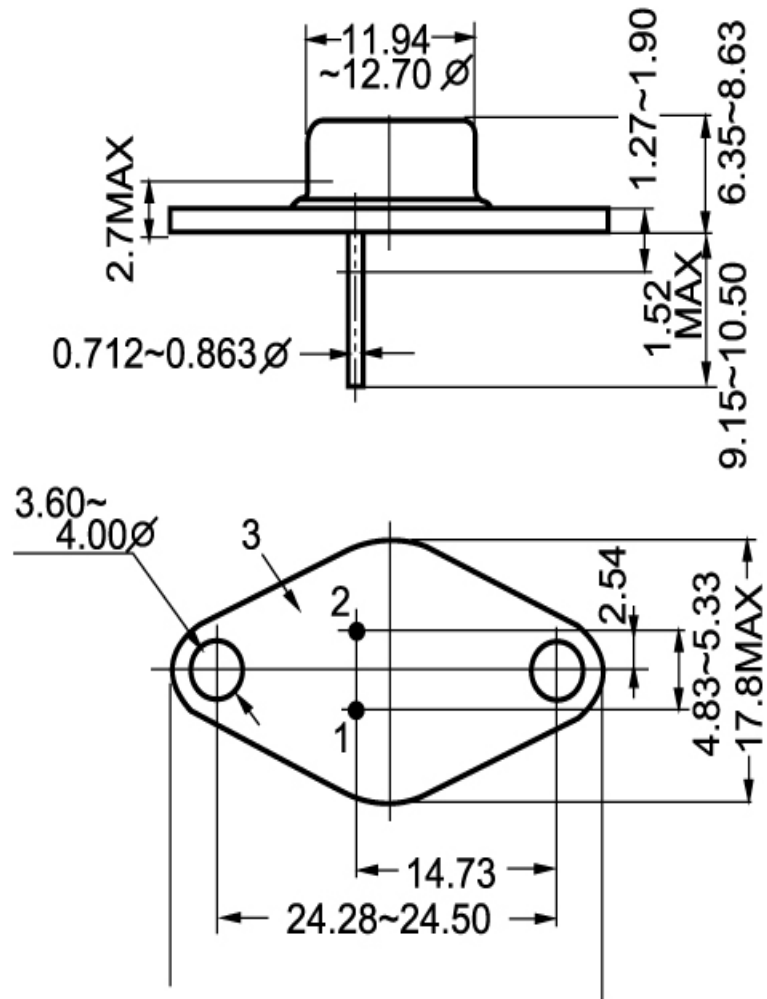


Fig.2 outline dimensions